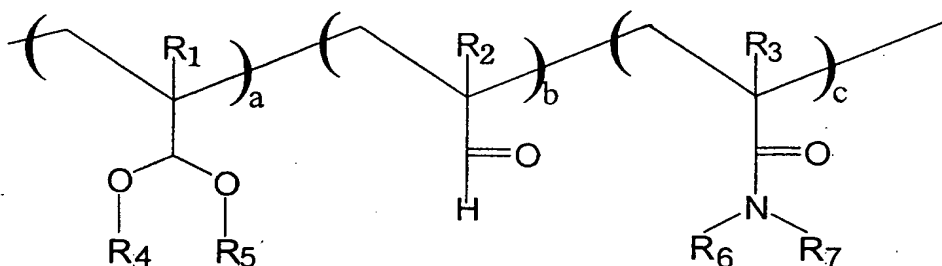


## ABSTRACT OF THE DISCLOSURE

Photoresist polymers and photoresist compositions containing the same are disclosed. A negative photoresist composition containing a photoresist polymer comprising a repeating unit represented by Formula 4 prevents collapse of patterns when photoresist patterns of less than 50nm are formed. Accordingly, the disclosed negative photoresist composition is very effective for a photolithography process using EUV (Extreme Ultraviolet, 13nm) light source.

Formula 4



wherein R<sub>1</sub>, R<sub>2</sub>, R<sub>3</sub>, R<sub>4</sub>, R<sub>5</sub>, R<sub>6</sub>, R<sub>7</sub>, a, b and c are as defined in the description.